ELECTRONICS, INC.
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NTE2307
Silicon NPN Transistor
High Gain Power Amp

DISCONTINUED

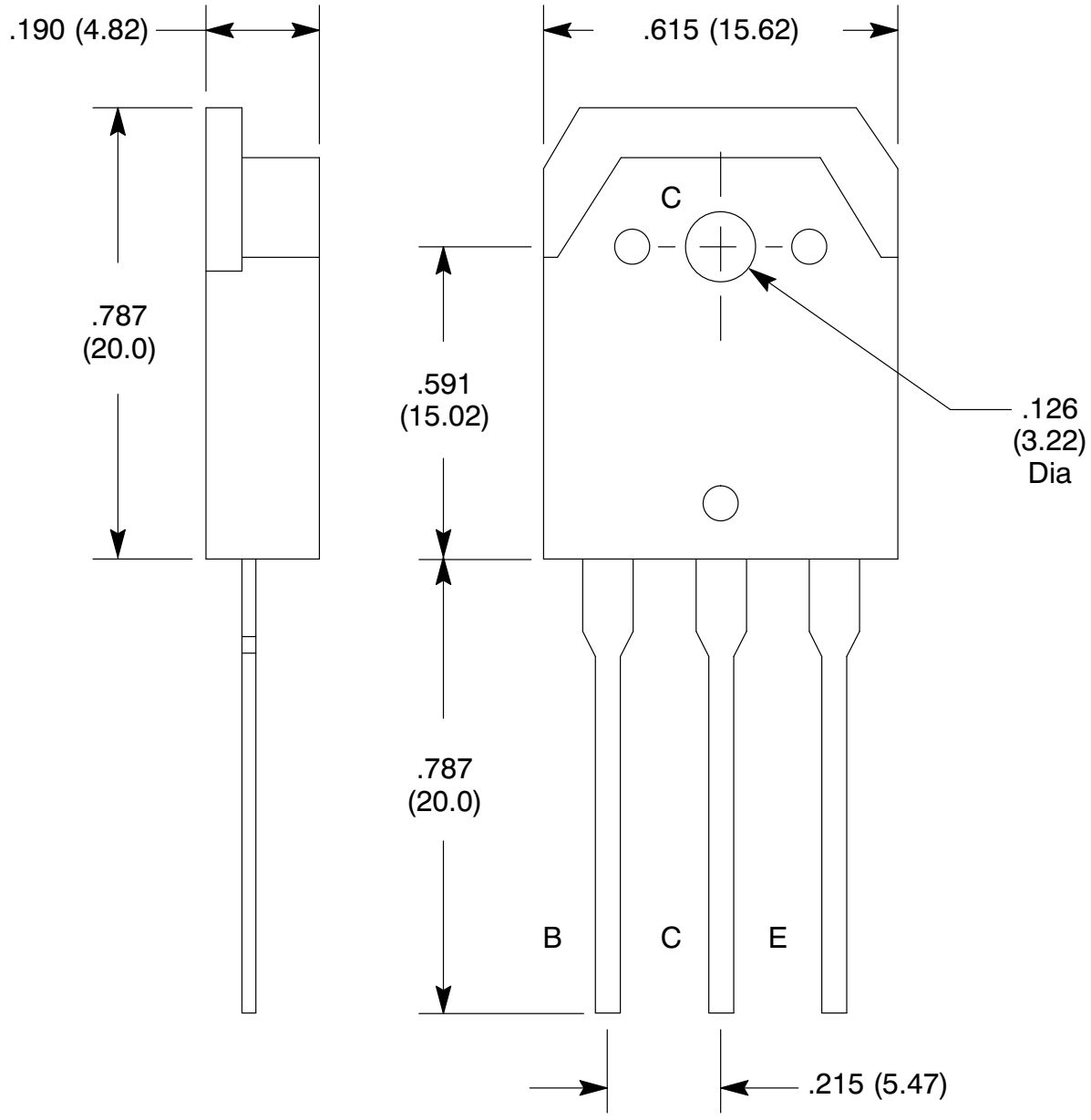
Features:
- High Voltage
- High DC Current Gain
- High Collector Power Dissipation Capability

Absolute Maximum Ratings: (T_A = +25°C unless otherwise specified)

Collector–Base Voltage, V_{CBO} 200V
Collector–Emitter Voltage, V_{CEO} 180V
Emitter–Base Voltage, V_{EBO} 5V
Collector Current, I_C 5A
Base Current, I_B 2A
Collector Power Dissipation (T_C = +25°C), P_C 80W
Operating Junction Temperature, T_J . . . . . +150°C
Storage Temperature Range, T_{stg} . . . . . –55° to +150°C

Electrical Characteristics: (T_A = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	V_{CB} = 200V, I_E = 0	–	–	100	μA
	I_{CEO}	V_{CE} = 180V, I_B = 0	–	–	10	mA
Emitter Cutoff Current	I_{EBO}	V_{EB} = 5V, I_C = 0	–	–	100	μA
Collector–Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C = 50mA, I_B = 0	180	–	–	V
DC Current Gain	h_{FE}	V_{CB} = 5V, I_C = 1A	500	–	2000	
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = 1A, I_B = 20mA	–	–	1.0	V
Base–Emitter Voltage	V_{BE}	V_{CE} = 5V, I_C = 1A	0.6	0.7	0.8	V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